

一、产品特点:

GJC650DA02是一款具有超高的开关频率、低栅极电荷、高功率密度的常关型(增强型)器件.

二、产品参数

Parameter	Value	Unit
VDS,max	650	V
RDS(on),max	200	mΩ
QG,typ	2	nC
IDS,Pulse	20	A
QOSS @ 400V	19	nC
Qrr	0	nC

Type/Ordering Code	Package	Marking
XGC650DA02	DFN 5X6	GJC650DA02



器件产品规格书

2、增强型功率器件-GJC650DA02

三、产品参数（静态）

Parameter	Symbol	Values			Unit	Note/Test Condition
		Min	Typ.	Max		
Gate threshold voltage	VGS(TH)	0.8	1.3	1.8	V	ID = 11 mA; VDS = VGS; Tj = 25 °C
		-	1.6	-	V	ID = 11 mA; VDS = VGS; Tj = 125 °C
Drain-source leakage current	IDSS	-	2	20	μA	VDS = 650 V; VGS = 0 V; Tj = 25 °C
		-	10	120	μA	VDS = 650 V; VGS = 0 V; Tj = 150 °C
Gate-source leakage current	IGSS	-	40	-	μA	VGS = 6 V; VDS = 0 V
Drain-source on-state resistance	RDS(on)	-	165	200	mΩ	VGS = 6 V; ID = 3 A; Tj = 25 °C
		-	322	-	mΩ	VGS = 6 V; ID = 3 A; Tj = 150 °C
Gate resistance	RG	-	1.5	-	Ω	F = 5 MHz; open drain

四、产品参数（动态）

Parameter	Symbol	Values			Unit	Note/Test Condition
		Min	Typ	Max		
Input capacitance	Ciss	-	73	-	pF	VGS = 0 V; VDS = 400 V; f = 100 kHz
Output capacitance	Coss	-	20	-	pF	VGS = 0 V; VDS = 400 V; f = 100 kHz
Reverse transfer capacitance	Crss	-	0.2	-	pF	VGS = 0 V; VDS = 400 V; f = 100 kHz
Effective output capacitance, energy related 1	Co(er)	-	27	-	pF	VGS = 0 V; VDS = 0 to 400 V
Effective output capacitance, time related 2	Co(tr)	-	43	-	pF	VGS = 0 V; VDS = 0 to 400 V
Output Charge	QOSS	-	19	-	nC	VGS = 0 V; VDS = 0 to 400 V

